

MA3S133

Silicon epitaxial planar type

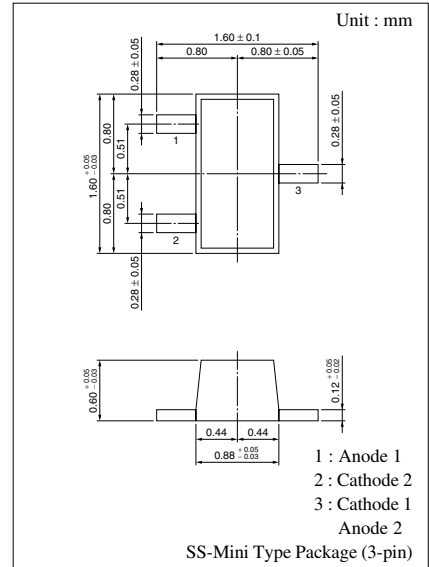
For switching circuits

■ Features

- Super-small SS-mini type package contained two elements, allowing high-density mounting
- Two diodes are connected in series in the package

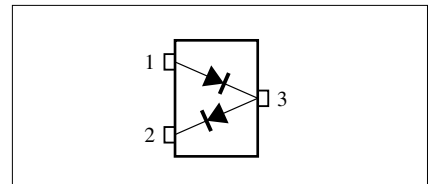
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Forward current (DC)	Single	I_F	mA
	Series		
Peak forward current	Single	I_{FM}	mA
	Series		
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: MP

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75\text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100\ \mu\text{A}$	80			V
Terminal capacitance	C_t^{*1}	$V_R = 0\text{ V}, f = 1\text{ MHz}$			5.5	pF
	C_t^{*2}	$V_R = 0\text{ V}, f = 1\text{ MHz}$			3.0	pF
Reverse recovery time ^{*3}	t_{rr}^{*1}	$I_F = 10\text{ mA}, V_R = 6\text{ V}$ $I_{tr} = 0.1 \cdot I_R, R_L = 100\ \Omega$		150		ns
	t_{rr}^{*2}	$I_F = 10\text{ mA}, V_R = 6\text{ V}$ $I_{tr} = 0.1 \cdot I_R, R_L = 100\ \Omega$		9		ns

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Between pins 2 and 3

*2 : Between pins 1 and 3

*3 : t_{rr} measuring circuit

